Amendments to the Specification:

Please replace the paragraph bridging pages 2 and 3 with the following amended paragraph:

In accordance with the present invention, in order to prevent a current from flowing due to reasons other than the carrier recombination, a volume resistivity of a thin film made of a light-emitting organic compound in an EL device is set to be in the range of 3×10^{10} Ωcm or larger. A volume resistivity of a thin film made of a light-emitting organic compound in an EL device is set to be in the range from 1×10^{11} to 1×10^{12} Ωcm (preferably, in the range from 1×10^{12} to 1×10^{13} Ωcm). In order to obtain the volume resistivity value in the above range, the concentration of ionic impurities contained in the thin film made of the light-emitting organic compound is set to be equal to 0.1 ppm or lower (preferably, equal to 0.01 ppm or lower). The ionic impurity refers to an element belonging to Group I or II in the periodic table, and typically to sodium (Na) or potassium (K).

Please replace the paragraph beginning on page 4, line 16, with the following amended paragraph:

As set forth above, in accordance with the present invention, a light-emitting organic compound containing ionic impurities at the concentration of 0.1 ppm or lower (preferably, at the concentration of 0.01 ppm or lower) is formed, and by using it, an EL device including a thin film made of a light-emitting organic compound having a volume resistivity in the range of 3×10^{10} Ωcm or larger. A volume resistivity of a thin film made of a light-emitting organic compound in an EL device is set to be in the range of 1×10^{11} to 1×10^{12} cm (preferably, in the range from 1×10^{12} to 1×10^{13} Ωcm) is formed so as to fabricate an EL display device by utilizing such an EL device.

Please replace the paragraph beginning at page 11, line 13, with the following amended paragraph:

In accordance with the present invention, the above-mentioned purification process is repeated so that the concentration of ionic impurities contained in the thin film made of the light-emitting organic compound reaches a level of 0.1 ppm or lower (preferably, a level of 0.01 ppm or lower). The above-mentioned concentration range of the ionic impurities provides the thin film made of the light-emitting organic compound, which functions as a light-emitting layer, with a volume resistivity in the range of 3×10^{10} Ωcm or larger. A volume resistivity of a thin film made of a light-emitting organic compound in an EL device is set to be in the range of 1×10^{11} to 1×10^{12} cm (preferably, in the range from 1×10^{12} to 1×10^{13} Ωcm). Thus, a current caused by reasons other than the carrier recombination is prevented from flowing.

Please replace the paragraph bridging pages 11 and 12 with the following amended paragraph:

In the case where the EL layer includes only a light-emitting layer, i.e., only a single layer of a thin film made of the light-emitting organic compound, the light-emitting layer is required to meet conditions in which the concentration of the contained ionic impurities is equal to or lower than 0.1 ppm (preferably, at 0.01 ppm or lower) and the volume resistivity is in the range of 3×10^{10} Ωcm or larger. A volume resistivity of a thin film made of a light-emitting organic compound in an EL device is set to be in the range from 1×10^{11} to 1×10^{12} Ωcm (preferably, in the range from 1×10^{12} to 1×10^{13} Ωcm).

Please replace the paragraph beginning at page 15 line 5 with the following amended paragraph:

In the EL display device having the above-mentioned construction in accordance with the present invention, the thin film made of the light-emitting organic compound contains ionic impurities at the concentration of 0.1 ppm or lower (preferably, at the concentration of 0.01 ppm or lower) and a volume resistivity in the range of 3×10^{10} Ωcm or larger. A volume resistivity of a thin film made of a light-emitting organic compound in an EL device is set to be in the range of 1×10^{11} to 1×10^{12} Ωcm (preferably, in the range from 1×10^{12} to 1×10^{13} Ωcm). Accordingly, a current caused by reasons other than the carrier recombination can be prevented from flowing through a thin film made of the light-emitting organic compound that is contained in an EL device, and deterioration caused by unnecessary heat generation can be prevented.

Please replace the paragraph beginning at page 29, line 4, with the following amended paragraph:

It should be noted that prior to the film formation of the above-mentioned organic compound, the purification process (typically, the dialysis method) is repeated at least three times or more, preferably five times or more, so that the concentration of the ionic impurities contained therein is reduced to 0.1 ppm or lower (preferably 0.01 ppm or lower). Thus, the concentration of the ionic impurities contained in the light-emitting layer 349 shown in Fig. 4C is reduced to 0.1 ppm or lower (preferably to 0.01 ppm or lower) and a volume resistivity of the light-emitting layer 349 is set in the range of 3×10^{10} Ωcm or larger. A volume resistivity of a thin film made of a light-emitting organic compound in an EL device is set to be in the range of 1×10^{11} to 1×10^{12} Ωcm (preferably, in the range from 1×10^{12} to 1×10^{13} Ωcm).

Please replace the paragraph beginning at page 36, line 15 with the following amended paragraph:

It should be noted that prior to the film formation of the above-mentioned organic compound, the purification process (typically, the dialysis method) is repeated at least three times or more, preferably five times or more, so that the concentration of the ionic impurities contained in the high-molecular type EL compound is reduced to 0.1 ppm or lower (preferably, to 0.01 ppm or lower). Thus, the concentration of the ionic impurities contained in the EL layer 703 is reduced to 0.1 ppm or lower (preferably, to 0.01 ppm or lower), and a volume resistivity of the EL layer 703 is set in the range of 3×10^{10} Ωcm or larger. A volume resistivity of a thin film made of a light-emitting organic compound in an EL device is set to be in the range of 1×10^{11} to 1×10^{12} Ωcm (preferably, in the range from 1×10^{12} to 1×10^{13} Ωcm).